

Surface Reconstructions and Bonding via the Electron Localization Function: The Case of Si(001)

L. De Santis,^{1,2} and R. Resta^{1,3}

¹*INFM – Istituto Nazionale di Fisica della Materia*

²*SISSA – Scuola Internazionale Superiore di Studi Avanzati, Via Beirut 4, 34014 Trieste, Italy*

³*Dipartimento di Fisica Teorica, Università di Trieste, Strada Costiera 11, 34014 Trieste, Italy*

The bonding pattern of a covalent semiconductor is disrupted when a surface is cut while keeping a rigid (truncated bulk) geometry. The covalent bonds are partly reformed (with a sizeable energy gain) when reconstruction is allowed. We show that the “electron localization function” (ELF)—applied within a first-principles pseudopotential framework—provides an unprecedented insight into the bonding mechanisms. In the unreconstructed surface one detects a partly metallic character, which disappears upon reconstruction. In the surface reformed bonds, the ELF sharply visualizes strongly paired electrons, similar in character to those of the bulk bonds.

I. INTRODUCTION

The driving mechanism for surface reconstructions of a covalent material is the tendency of low-coordinated surface atoms to saturate dangling bonds. It is then obvious that a completely different bonding pattern differentiates the unreconstructed (*i.e.* bulk terminated) surface from the reconstructed one. When several different reconstructions are compared, these show in turn different bonding features. First-principles electronic structure calculations have provided over the years a major insight into these phenomena: however, the major tools used in investigating bonding at large has been the analysis of either the electronic charge density or the projected density of states. Since a few years a much more informative tool has been introduced in the quantum chemical literature to deal in a quantitative way with bonding features: this goes under the name of “electron localization function” (ELF).^{1–3} Although bonding at a reconstructed surface looks like an ideal arena for an ELF investigation, we are aware of only one such study, which however is performed at the non-selfconsistent tight-binding level.⁴ We present here a state-of-the-art thorough investigation about a paradigmatic case: namely, the silicon (001) surface. We show that the insight into the nature of bonding at the surface is very accurate and clear when the ELF is analyzed. We demonstrate—through a series of contour plots in high-symmetry planes—the outstanding ability of ELF in discriminating between the surface bonds occurring upon dimerizations at the Si(001) surface, thus providing an unprecedented insight into the physical mechanisms which drive the reconstruction. Dangling orbitals and surface bonds are visualized with a resolution incomparably sharper than by using the current tools, such as charge-density plots or projected densities of states.

We are using here the approach which has become the “standard model” in first-principle studies of covalent semiconductors:⁵ namely, density-functional theory (DFT)^{6–8} with norm-conserving pseudopotentials.⁹ This

approach has got a dominant role in the literature because of many of its key features, but ELF investigations within it have been quite scarce so far: ELF has been originally proposed as an all-electron tool, and as such has been mostly applied. Instead, we are going to show in the present work that by getting rid of the core electrons and focussing on the bonding electrons only, one makes the ELF message particularly perspicuous.

We study here an elemental system, where the key issue is metallic versus covalent bonding. Since the early days of electronic-structure theory, we understand bonding in simple metals through the paradigm of pseudopotential perturbation theory:^{10,11} the valence electrons behave basically as a free-electron gas in the region outside the ionic cores. At the opposite extreme, we understand covalent bonding through the paradigm of the H₂ molecule, whose electrons are strongly paired in a singlet state; in a more general case, covalent bond is characterized by “localization” of valence-electron pairs in appropriate regions of space. While charge-density plots do not help much in discriminating metallic from covalent, the ELF provides a quantitative measure of “metallicity” vs. “covalency” of a given bond, or more generally of a given valence region of the system. This measure is particularly significant in a pseudopotential framework where—amongst other things—a simple metal immediately displays the free-electron nature of its valence electrons. We furthermore observe that ELF is by definition an orbital-free approach: this feature is preserved when a first-principle framework (as opposed to a tight-binding one) is adopted, as it is done here.

The case study chosen for this work is possibly the theoretically best known semiconductor surface. Its most relevant features are therefore very well understood in the literature: in particular, the unreconstructed surface is metallic and the reconstructed one is insulating.¹² The aim of the present paper is not to demonstrate anything at variance with the common wisdom. Instead, our aim is to show how the known features of this surface can be recovered in a simple and meaningful way from an ELF analysis. It is also worth to stress that the ELF *does*

not make use of the spectrum of the system, while instead is a pure ground state property. In perspective, we are proposing ELF, in a modern pseudopotential framework,^{5,9} as a powerful tool for investigating bonding between over- or under-coordinated atoms in more complex, and worse known, situations.

II. ELECTRON LOCALIZATION FUNCTION

ELF was originally introduced by Becke and Edgecombe as a measure of the conditional probability of finding an electron in the neighborhood of another electron with the same spin. Starting from the short-range behavior of the parallel-spin pair probability, they defined a scalar function, conveniently ranging from zero to one, that uniquely identifies regions of space where the electrons are well localized, as occurs in bonding pairs or lone-electron pairs. By definition, ELF is identically one either in any single-electron wavefunction or in any two-electron singlet wavefunction: in both cases the Pauli principle is ineffective, and the ground wavefunction is nodeless or, loosely speaking, “bosonic”. In a many-electron system ELF is close to one in the regions where electrons are paired to form a covalent bond, while is small in low-density regions; ELF is also close to one where the unpaired lone electron of a dangling bond is localised. Furthermore, since in the homogeneous electron gas ELF equals 0.5 at any density, values of this order in inhomogeneous systems indicate regions where the bonding has a metallic character.

A major advance is the ELF reformulation due to Savin *et al.*,¹³ which is adopted in the present work. Owing to the Pauli principle, the ground-state kinetic energy density of a system of fermions is no smaller than the one of a system of bosons at the same density: ELF can be equivalently expressed in terms of the Pauli excess energy density, thus making no explicit reference to the pair distribution. This is particularly convenient in our case, since the pair density is outside the scope of DFT. The Savin *et al.* reformulation also provides a meaningful physical interpretation: where ELF is close to its upper bound, electrons are strongly paired and the electron distribution has a local “bosonic” character.

The definition of ELF is:

$$\mathcal{E}(\mathbf{r}) = \frac{1}{1 + [D(\mathbf{r})/D_h(\mathbf{r})]^2}, \quad (1)$$

thus taking by design values between zero and one. Following Savin *et al.*, $D(\mathbf{r})$ is the Pauli excess kinetic energy density, defined as the difference between the kinetic energy density and the so-called von Weizsäcker kinetic energy functional:¹⁴

$$D(\mathbf{r}) = \frac{1}{2} \nabla_{\mathbf{r}} \nabla_{\mathbf{r}'} \rho(\mathbf{r}, \mathbf{r}') \Big|_{\mathbf{r}=\mathbf{r}'} - \frac{1}{8} \frac{|\nabla n(\mathbf{r})|^2}{n(\mathbf{r})} \quad (2)$$

where ρ is the one-body reduced (spin-integrated) density matrix. The von Weizsäcker functional provides

a rigorous lower bound for the exact kinetic energy density¹⁴ and is ordinarily indicated as the “bosonic” kinetic energy, since it coincides with the ground-state kinetic energy density of a non-interacting system of bosons at density $n(\mathbf{r})$. Therefore, D is positive semidefinite and provides a direct measure of the local effect of the Pauli principle. The other ingredient of Eq. (1) is $D_h(\mathbf{r})$, defined as the kinetic energy density of the homogeneous electron gas at a density equal to the local density:

$$D_h(\mathbf{r}) = \frac{3}{10} (3\pi^2)^{\frac{2}{3}} n(\mathbf{r})^{\frac{5}{3}}. \quad (3)$$

It is obvious to verify that the function $\mathcal{E}$ is identical to one in the ground state of any two-electron system, while is identical to 0.5 in the homogeneous electron gas at any density.

As commonly done in many circumstances—including in other ELF investigations¹³—we approximate the kinetic energy of the interacting electron system with the one of the noninteracting Kohn-Sham (KS) one. We therefore use the KS density matrix:

$$\rho(\mathbf{r}, \mathbf{r}') = 2 \sum_i \phi_i^{KS}(\mathbf{r}) \phi_i^{*KS}(\mathbf{r}'), \quad (4)$$

where $\phi_i^{KS}(\mathbf{r})$ are the occupied KS orbitals. Such approximation is expected to become significantly inaccurate only in the case of highly correlated materials.

The original ELF definition is an all-electron one, and has the remarkable feature of naturally revealing the entire shell structure for heavy atoms. Such a feature is of no interest here, since only one electronic shell (the *sp* valence one) is involved in the bonding of Si atoms in any circumstances. The pseudopotential scheme simplifies the landscape, since only the electrons of the relevant valence shell are dealt with explicitly: the ELF message comes out therefore much clearer, with basically no loss of information.¹⁵ In the spatial regions occupied by core electrons, the pseudo-electronic distribution shows a depletion and ELF assumes very low values. Outside the ionic cores, in the regions relevant to chemical bonding, the norm conservation endows the pseudocharge density with physical meaning, as widely discussed in the modern pseudopotential literature:^{5,9} in the specific case of Si, there is an experience of about 20 years in dealing with a plethora of different physical problems. By the same token of norm conservation, even the pseudo-orbitals—and hence their kinetic energy density—closely map the all-electron ones in the bonding regions. The pseudo ELF carries therefore—in the material of interest here—the same information as the all-electron ELF, while it removes irrelevant and confusing features due to the inner, chemically inert, shells.

III. CALCULATIONS

The (001) silicon surface is strongly reconstructed, with several different reconstructed structures. A relatively simple (2×1) reconstruction is formed by surface atoms moving together in pairs to form dimers.

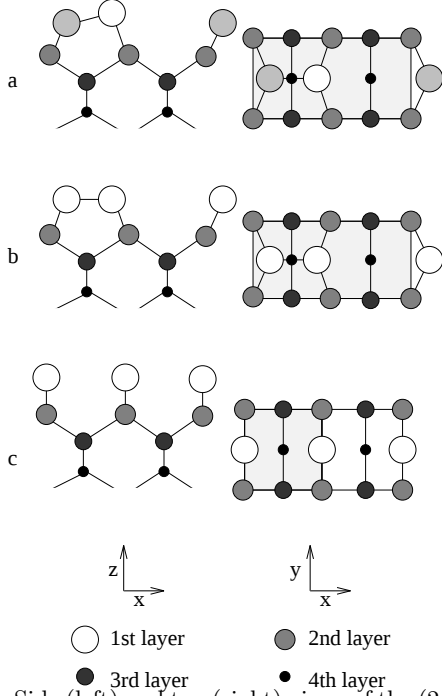


FIG. 1. Side (left) and top (right) views of the (2×1) reconstructions of the Si(001) surface. (a) Buckled-dimer, (b) symmetric-dimer, and (c) ideal (bulk-terminated) surface. The atoms in the first four layers are shown, with symbols as indicated in the figure bottom. The surface unit cells (shaded areas) are also shown.

The driving force for the dimer formation is the elimination of a dangling bond from the surface atoms. Each atom of the unreconstructed surface is bonded to only two neighbours and therefore has two dangling bonds projecting out of the surface. If the atoms move together in pairs, forming a new bond between them, then one of these dangling bonds will be eliminated from each member of the pair. This leads to a considerable energy gain since half of the broken surface bonds are reconstructed. The buckled dimer model is a simple modification of the dimer model in which each dimer is tilted or “buckled” out of the plane of the surface. We have considered therefore the unreconstructed and the (2×1) symmetric and buckled dimer surfaces, in order to better understand the connection between surface reconstruction and electronic localization. A schematic side and top view of these three surfaces is shown in Fig. 1.

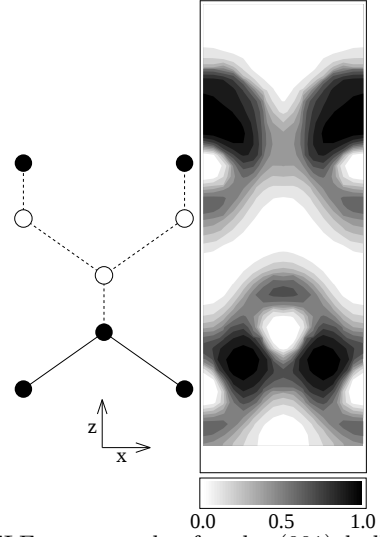


FIG. 2. ELF contour plot for the (001) bulk terminated silicon surface, in the plane containing two nearest-neighbor atoms: the relative dangling orbitals are revealed by the black ELF regions. The grey-scale is also shown: dark (clear) regions correspond to large (small) ELF values. In the schematic side view, black balls and solid lines correspond, respectively, to in-plane atoms and bonds; white balls and dashed lines to off-plane atoms and bonds.

All the calculation use quite standard ingredients: a plane-wave expansion of the KS orbitals with a 10 Ry kinetic-energy cut-off, 16 $\mathbf{k}$ -points on a Monkhorst and Pack¹⁶ mesh for the irreducible Brillouin zone integration, and a norm-conserving pseudopotential in fully non-local form.¹⁷ All our calculations were performed in a supercell geometry where the surface is modeled by a finite-size slab periodically repeated in the direction normal to the surface. For the ideal (bulk terminated) surface we use a unit cell containing 11 layers of atoms separated by the equivalent of 13 atomic layers of vacuum. For the symmetric and buckled dimer (2×1) surface, we have reproduced the Roberts and Needs¹⁸ calculation, using directly their relaxed atomic coordinates.

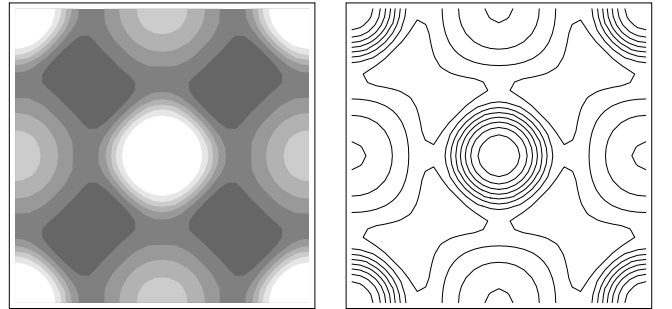


FIG. 3. Contour plots for bulk aluminum in the [100] crystalline plane. Left panel: ELF, where the same grey-scale as in all ELF figures is adopted. Right panel: pseudocharge density.

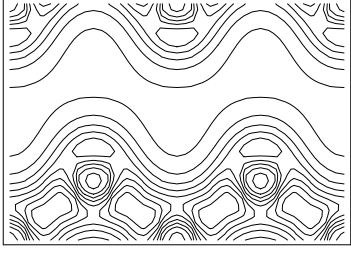


FIG. 4. Pseudocharge density contour plot for bulk silicon in the same crystallographic plane as for Fig. 2.

We show in Fig. 2 the ELF contour plot for the unreconstructed surface, in the plane containing the dangling orbitals and two nearest neighbor surface atoms. As already discussed above, pseudoatoms correspond to the white regions (ELF minima). Before discussing the surface results, we pause to illustrate the bulk features and the capability of ELF in discriminating between metallic and covalent bonding.

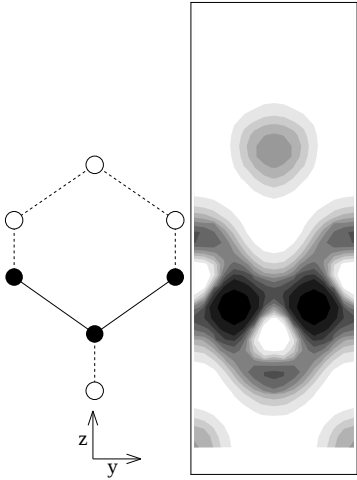


FIG. 5. ELF contour plot for the (001) bulk terminated silicon surface. Plane orthogonal to the dangling bond, passing through the center of the surface unit cell. For the schematic side view, symbols as in Fig. 2.

In the bulk Si region, one clearly sees the almost black regions in Fig. 2 between nearest-neighbor atoms, whose bonding pattern in this geometry has the shape of a “zig-zag” chain. In these bonding regions our calculated ELF attains the maximum value of 0.96, thus indicating that the Pauli principle has little effect. In agreement with a chemical picture of the covalent bond, we associate these regions to the opposite-spin electron pairs—actually a “bosonic” system—localized between every pair of bonded atoms. This is to be contrasted to metallic bonding, where the valence electrons have a free-electron nature: to make this point better clear, we take as an example a paradigmatic simple metal: crystalline aluminum, whose bulk ELF is shown in the left panel of Fig. 3 to the same grey scale. Comparing this plot

with the bulk region of silicon in Fig. 2 we immediately appreciate the spectacular ELF ability to distinguish in a very clearcut way between metallic bonding and covalent bonding. The ELF plot in aluminum shows—outside the core regions—a large grey area, which correspond to a jellium-like (or Thomas-Fermi) ELF value. Actually, the maximum value attained by $\mathcal{E}(\mathbf{r})$ between nearest-neighbor atoms is only 0.61.

Comparison of the two ELF plots provides therefore the most significant and perspicuous visualization of the important *qualitative* difference between the covalent bond and the metallic one. In the bulk of the two materials the Pauli principle plays quite a different role. The other typical tools for analysis, such as charge-density plots or projected density of states, lack by far a similar sharpness. As an example, we show the corresponding pseudocharge density plots in the right panel of Fig. 3 (aluminum) and in Fig. 4 (silicon). From such figures, hardly any information about metallicity or covalency can be drawn.

IV. RESULTS

We now move to discuss the surface results. Focussing on the surface region in Fig. 2, one notices that the two dangling orbitals are also well visualized by the ELF plot: every dangling bond is associated to an *isolated* electron, thus corresponding to an high ELF value. However, a more striking bonding feature of the same unreconstructed Si(001) surface is detected when analyzing ELF in the orthogonal plane, passing midway between two nearest neighbor surface atoms (Fig. 5). There is a grey “fermionic channel”—defined as a region where ELF is of the order of 0.5—between the two nonbonded atoms: this channel in the midpoint has a perfect circular section, but it is actually formed by two grey-ELF strips going round the surface atoms and intersecting at the midpoint, as clearly shown by a top view (left panel of Fig. 6).

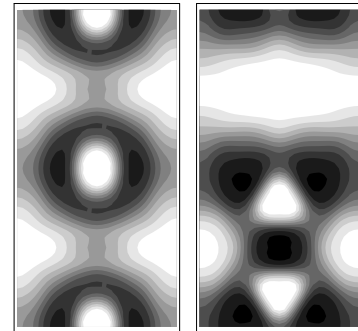


FIG. 6. ELF contour plot for the Si(001) bulk terminated (left panel) and symmetric-dimer reconstructed (right panel). Surface plane passing through the topmost atoms.

The presence of this extended metallic-like system

along the unrelaxed surface must be connected to the strong surface strain, due to the nonbonded atoms. As soon as the surface is relaxed and the dimer formation is allowed, there is a strong surface “bosonization”, associated with a sizeable reduction of the fermionic channel. This localization effect due to the dimerization process is perspicuously shown in Fig. 6, where the unreconstructed situation is compared to the reconstructed one, for the symmetric-dimer case. The metallic character of the unreconstructed surface, and the insulating character of the reconstructed one, are well documented in the literature.¹² What is remarkable here is that ELF visualizes such characters without using *any* spectral information about the system.

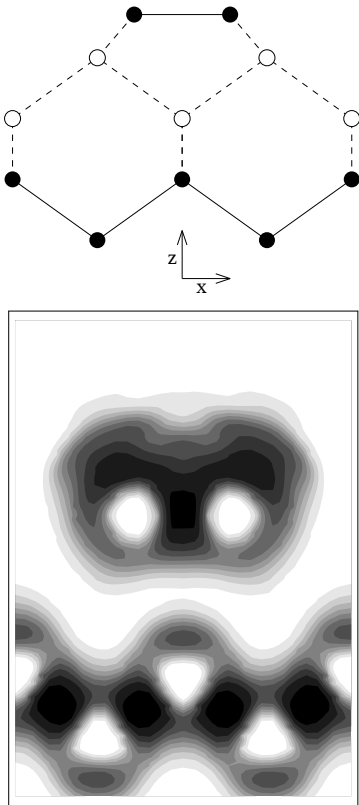


FIG. 7. ELF contour plot for the Si(001) (2×1) symmetric-dimer surface. Plane orthogonal to the surface, containing the dimer. For the schematic side view, symbols as in Fig. 2.

A more detailed analysis of the ELF variations induced by rebonding at the surface is provided by Fig. 7 for the symmetric-dimer case and in Fig. 8 for the buckled-dimer one, both drawn in the plane passing through the surface atoms, and to be compared to the analogous plot of Fig. 2 for the unreconstructed case. In both cases the dimer has a strongly covalent bond character and is surrounded by a region of high ELF values: such localization effect is clearly connected to the surface reduced coordination, since the ELF around the isolated topmost atoms has a more pronounced atomic character.¹⁹

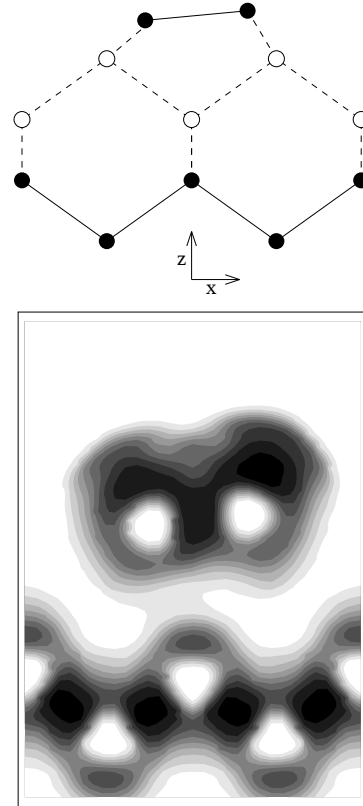


FIG. 8. ELF contour plot for the Si(001) (2×1) buckled dimer surface. Plane orthogonal to the surface, containing the dimer. For the schematic side view, symbols as in Fig. 2.

In conclusion, we have shown how the electronic system at a paradigmatic semiconductor surface changes its character upon reconstruction. ELF clearly visualizes how electron pairing accompanies rebonding. In the unreconstructed surface, besides the dangling-bond electrons, we have detected channels of metallic-like character in the surface plane. Both features disappear upon reconstruction.

-
- ¹ A. D. Becke, K. E. Edgecombe, J. Chem. Phys. **92**, 5397 (1990).
 - ² B. Silvi, A. Savin, Nature **371**, 683 (1994).
 - ³ A. Savin, R. Nesper, S. Wengert and T. F. Fässler, Angew. Chem. Int. Ed. Engl. **36**, 1808 (1997).
 - ⁴ T. F. Fässler, U. Häussermann and R. Nesper, Chem. Eur. J. **1**, 625 (1995).
 - ⁵ M.L. Cohen, in *Electronic Materials*, edited by J.R. CheLIKowsky and A. Franciosi (Springer, Berlin, 1991), p.57.
 - ⁶ P. Hohenberg and W. Kohn, Phys. Rev. **136** B864 (1964).
 - ⁷ W. Kohn and L. J. Sham, Phys. Rev. **140**, A1133 (1965).
 - ⁸ *Theory of the Inhomogeneous Electron Gas*, edited by S. Lundqvist and N.H. March (Plenum, New York, 1983).
 - ⁹ W. E. Pickett, Comput. Phys. Rep. **9**, 115 (1989).

- ¹⁰ W.A. Harrison, *Pseudopotentials in the Theory of Metals* (Benjamin, New York, 1966).
- ¹¹ V. Heine, in *Solid State Physics*, edited by H. Ehrenreich, F. Seitz, and D. Turnbull, vol **24** (Academic, New York, 1970), p.1; M.L. Cohen and V. Heine, *ibid.* p.250.
- ¹² J. Dabrowski and M. Scheffler, *Appl. Surf. Sci.* **56–58**, 15 (1992).
- ¹³ A. Savin, O. Jepsen, J. Flad, O. K. Andersen, H. Preuss and H. G. von Schneiring, *Angew. Chem. Int. Ed. Engl.* **31**, 187 (1992).
- ¹⁴ R.M. Dreizler and E.K.U. Gross, *Density Functional Theory: an Approach to the Quantum Many-body Problem* (Springer, Berlin, 1990).
- ¹⁵ M. Kohout and A. Savin, *J. Comp. Chem.* **18**, 1431 (1997).
- ¹⁶ H. J. Monkhorst and J. D. Pack, *Phys. Rev. B* **13**, 5188 (1976).
- ¹⁷ L. Kleinman and D. M. Bylander, *Phys. Rev. Lett.* **48**, 1425 (1982).
- ¹⁸ N. Roberts and R. J. Needs, *Surf. Sci.* **236**, 112 (1990).
- ¹⁹ In a free pseudoatom, ELF has spherical symmetry with a single maximum in the valence-shell region.